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Kind regards,

Team Nexperia



# PMEG4015EPK

# 40 V, 1.5 A low VF MEGA Schottky barrier rectifier Rev. 2 — 6 March 2012

Product data sheet

#### **Product profile** 1.

## 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD1608 (DFN1608D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

#### 1.2 Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 1.5 A
- Reverse voltage: V<sub>R</sub> ≤ 40 V
- Low forward voltage V<sub>F</sub> ≤ 610 mV
- Low reverse current

- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

### 1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions		Min	Тур	Max	Unit
average forward current	$\delta$ = 0.5; f = 20 kHz; $T_{amb} \le 65$ °C; square wave	[1]	-	-	1.5	Α
	$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 135 °C; square wave		-	-	1.5	Α
reverse voltage	T <sub>j</sub> = 25 °C		-	-	40	V
forward voltage	$I_F$ = 1.5 A; pulsed; $t_p \le 300~\mu s; \delta \le 0.02;$ $T_j$ = 25 °C		-	540	610	mV
reverse current	$V_R = 10 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	1	5	μΑ
reverse recovery time	$I_R$ = 0.5 A; $I_F$ = 0.5 A; $I_{R(meas)}$ = 0.1 A; $T_j$ = 25 °C		-	4	-	ns
	average forward current  reverse voltage forward voltage reverse current	$ \begin{array}{ll} \text{average forward} & \delta = 0.5; \ f = 20 \ \text{kHz}; \ T_{amb} \leq 65 \ ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \delta = 0.5; \ f = 20 \ \text{kHz}; \ T_{sp} \leq 135 \ ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \text{reverse voltage} & T_j = 25 \ ^{\circ}\text{C} \\ \hline \text{forward voltage} & I_F = 1.5 \ \text{A}; \ \text{pulsed}; \ t_p \leq 300 \ \mu\text{s}; \ \delta \leq 0.02; \\ \hline T_j = 25 \ ^{\circ}\text{C} \\ \hline \text{reverse current} & V_R = 10 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \text{reverse recovery time} & I_R = 0.5 \ \text{A}; \ I_{R(meas)} = 0.1 \ \text{A}; \\ \hline \end{array} $	average forward current	$\begin{array}{c} \text{average forward} \\ \text{current} \\ \end{array} \begin{array}{c} \delta = 0.5; \ f = 20 \ \text{kHz}; \ T_{amb} \leq 65 \ ^{\circ}\text{C}; \\ \text{square wave} \\ \\ \hline \delta = 0.5; \ f = 20 \ \text{kHz}; \ T_{sp} \leq 135 \ ^{\circ}\text{C}; \\ \text{square wave} \\ \end{array} \begin{array}{c} - \\ \text{reverse voltage} \\ \hline T_j = 25 \ ^{\circ}\text{C} \\ \\ \hline forward voltage \\ \hline I_F = 1.5 \ \text{A}; \ \text{pulsed}; \ t_p \leq 300 \ \mu\text{s}; \ \delta \leq 0.02; \\ \hline T_j = 25 \ ^{\circ}\text{C} \\ \hline \text{reverse current} \\ \hline V_R = 10 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ \text{reverse recovery time} \\ \hline I_R = 0.5 \ \text{A}; \ I_F = 0.5 \ \text{A}; \ I_{R(meas)} = 0.1 \ \text{A}; \\ \hline \end{array} \begin{array}{c} - \\ - \\ - \\ - \\ \end{array}$	$ \begin{array}{c} \text{average forward} \\ \text{current} \\ \end{array} \begin{array}{c} \delta = 0.5;  f = 20   \text{kHz};  T_{amb} \leq 65  ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \delta = 0.5;  f = 20   \text{kHz};  T_{sp} \leq 135  ^{\circ}\text{C}; \\ \text{square wave} \\ \end{array} \begin{array}{c} - \\ - \\ \text{square wave} \\ \end{array} \\ \hline \text{reverse voltage} \\ T_j = 25  ^{\circ}\text{C} \\ T_j = 25  ^{\circ}\text{C} \\ \hline \text{reverse current} \\ V_R = 10  \text{V};  T_j = 25  ^{\circ}\text{C} \\ \hline \text{reverse recovery time} \\ I_R = 0.5  \text{A};  I_{R(meas)} = 0.1  \text{A}; \\ \end{array} \begin{array}{c} - \\ - \\ 1 \\ - \\ 4 \\ \end{array} $	$ \begin{array}{c} \text{average forward} \\ \text{current} \\ \end{array} \begin{array}{c} \delta = 0.5;  f = 20   \text{kHz};  T_{amb} \leq 65  ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \delta = 0.5;  f = 20   \text{kHz};  T_{sp} \leq 135  ^{\circ}\text{C}; \\ \text{square wave} \\ \end{array} \begin{array}{c} - \\ 1.5 \\ \text{square wave} \\ \end{array} \\ \hline \text{reverse voltage} \\ T_{j} = 25  ^{\circ}\text{C} \\ \text{forward voltage} \\ T_{j} = 25  ^{\circ}\text{C} \\ \hline \text{reverse current} \\ V_{R} = 10  \text{V};  T_{j} = 25  ^{\circ}\text{C} \\ \hline \text{reverse recovery time} \\ T_{R} = 0.5  \text{A};  I_{R(meas)} = 0.1  \text{A}; \\ \end{array} \begin{array}{c} 11 \\ - \\ - \\ 1.5 \\ $

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		. 84 .
2	A	anode	1 2	1 <del>    </del> 2 sym001
			Transparent top view	
			SOD1608 (DFN1608D-2)	

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

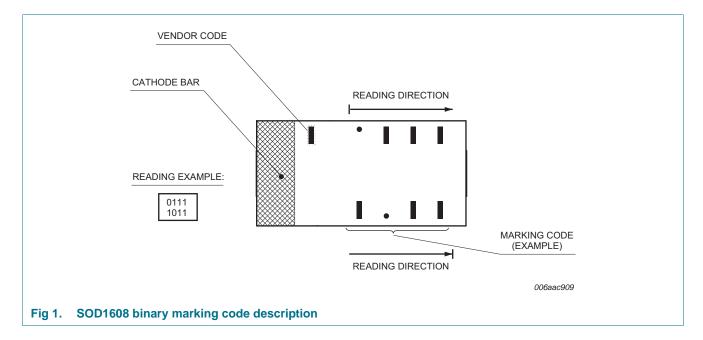
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG4015EPK	DFN1608D-2	Leadless ultra small plastic package; 2 terminals	SOD1608

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG4015EPK	0110 0000



## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C		-	40	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 130 °C		-	2.1	А
$I_{F(AV)}$	average forward current	$\delta$ = 0.5; f = 20 kHz; square wave; T <sub>amb</sub> ≤ 65 °C	<u>[1]</u>	-	1.5	Α
		$\delta$ = 0.5; f = 20 kHz; square wave; T <sub>sp</sub> ≤ 135 °C		-	1.5	Α
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \delta \le 0.25$		-	4	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p = 8 \text{ ms}; T_{j(init)} = 25 \text{ °C}; \text{ square wave}$		-	5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2][3]	-	415	mW
			[4][3]	-	895	mW
			[1][3]	-	1565	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fro	thermal resistance	in free air [1][2][3] [1][4][3] [1][5][3]	[1][2][3]	-	-	300	K/W
	from junction to ambient		-	-	140	K/W	
	ambient		-	-	80	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[6]	-	-	20	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub>are a significant part of the total power losses.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Reflow soldering is the only recommended soldering method.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

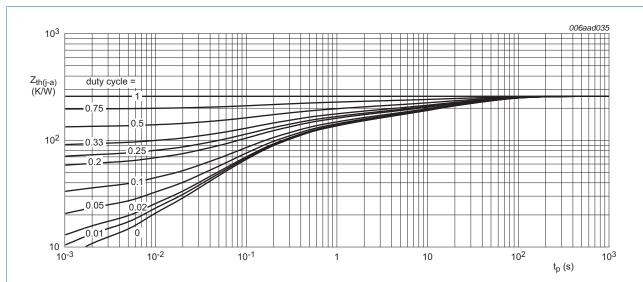
<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Reflow soldering is the only recommended soldering method.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

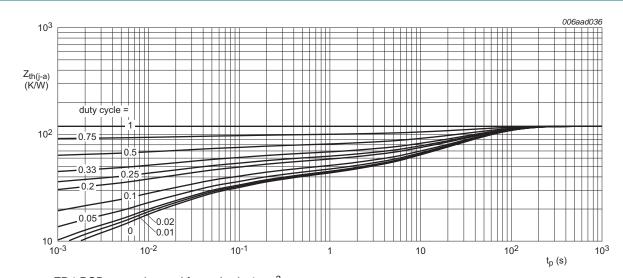
<sup>[5]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[6]</sup> Soldering point of cathode tab.



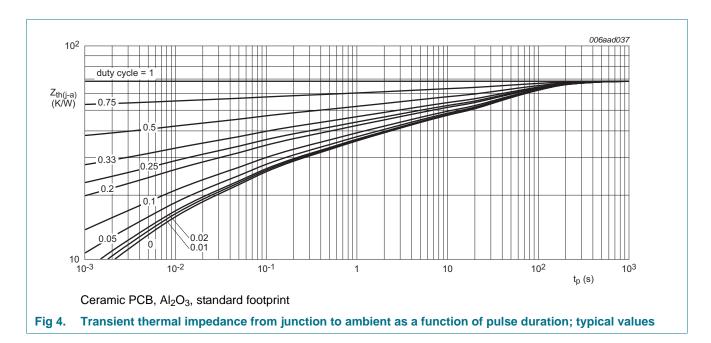
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

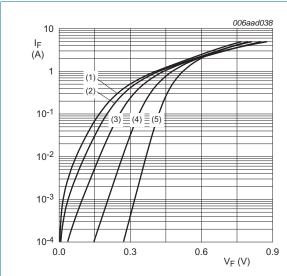
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F$ = 100 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	330	380	mV
		$I_F$ = 500 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	415	480	mV
		$I_F$ = 1 A; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C	-	490	550	mV
		$I_F$ = 1.5 A; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	540	610	mV
I <sub>R</sub>	I <sub>R</sub> reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	1	5	μA
		$V_R = 40 \text{ V}; T_j = 25 \text{ °C}$	-	8	30	μA
C <sub>d</sub>	diode capacitance	$V_R = 1 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C}$	-	75	90	pF
		$V_R = 10 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	30	40	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4	-	ns
$V_{FRM}$	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	440	-	mV



- (1)  $T_i = 150 \, ^{\circ}C$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \, ^{\circ}C$
- (4)  $T_j = 25 \, ^{\circ}C$
- (5)  $T_j = -40 \, ^{\circ}\text{C}$

Fig 5. Forward current as a function of forward voltage; typical values

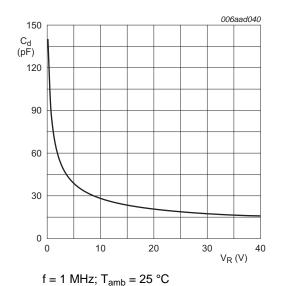
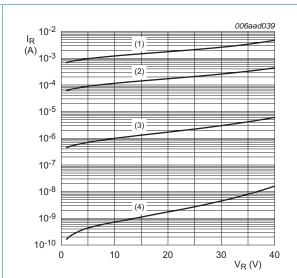
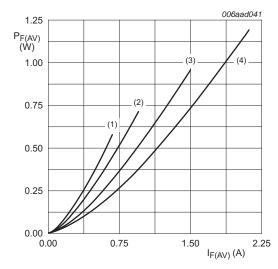


Fig 7. Diode capacitance as a function of reverse voltage; typical values



- (1)  $T_i = 125 \, ^{\circ}C$
- (2)  $T_i = 85 \, ^{\circ}C$
- (3)  $T_j = 25 \, ^{\circ}C$
- (4)  $T_i = -40 \, ^{\circ}C$

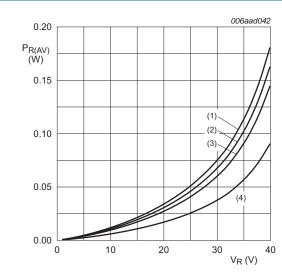
Fig 6. Reverse current as a function of reverse voltage; typical values



T<sub>i</sub> = 150 °C

- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

Fig 8. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 125 °C

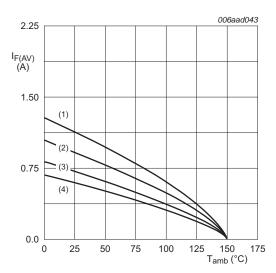
(1)  $\delta = 1$ 

(2)  $\delta = 0.9$ 

(3)  $\delta = 0.8$ 

(4)  $\delta = 0.5$ 

Fig 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_i = 150 \, ^{\circ}C$ 

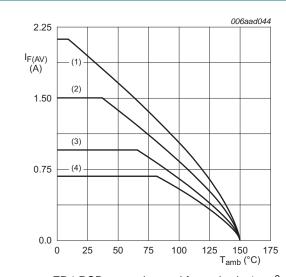
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1  $\mbox{cm}^2$ 

T<sub>i</sub> = 150 °C

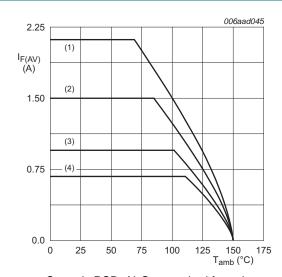
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

 $T_i = 150 \, ^{\circ}C$ 

(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

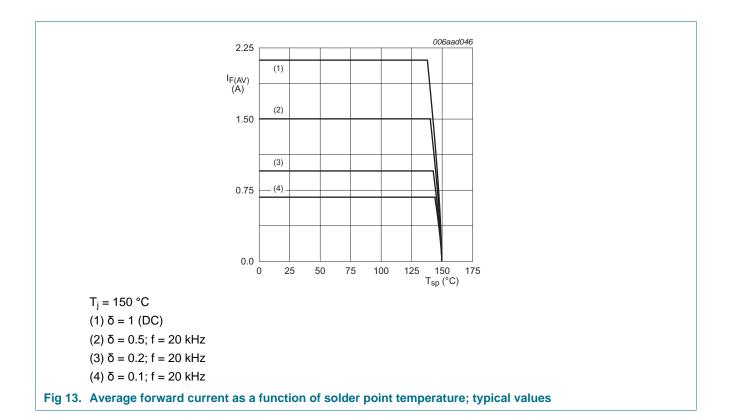
(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of ambient temperature; typical values

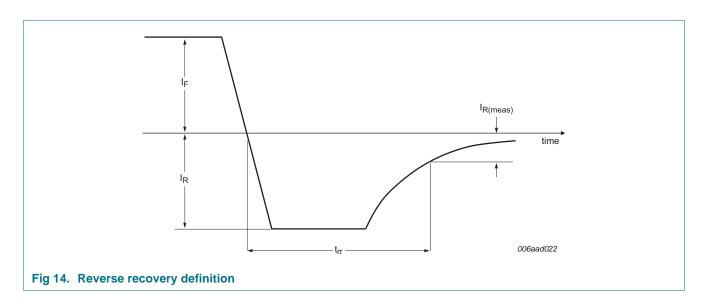
PMEG4015EPK

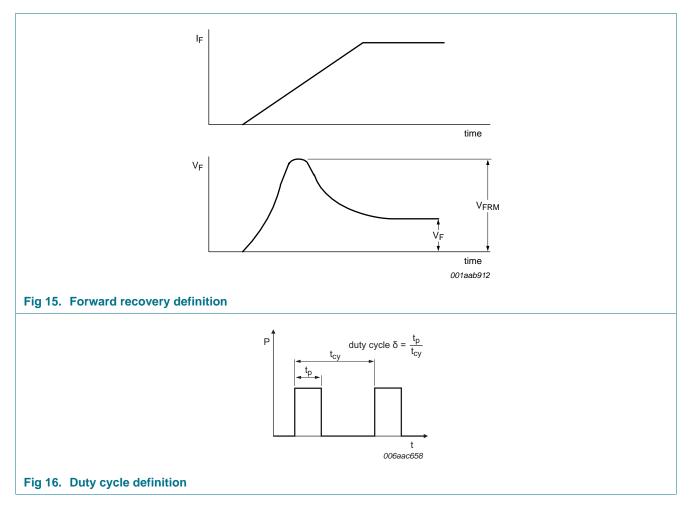
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## 8. Test information



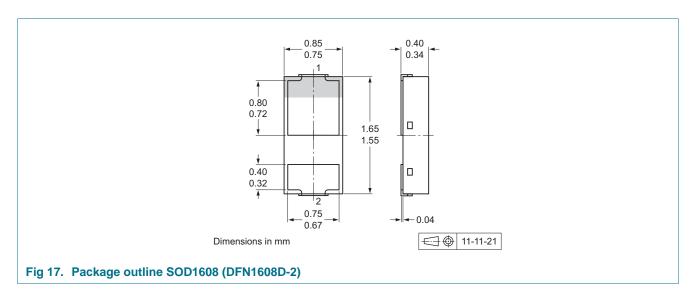


The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

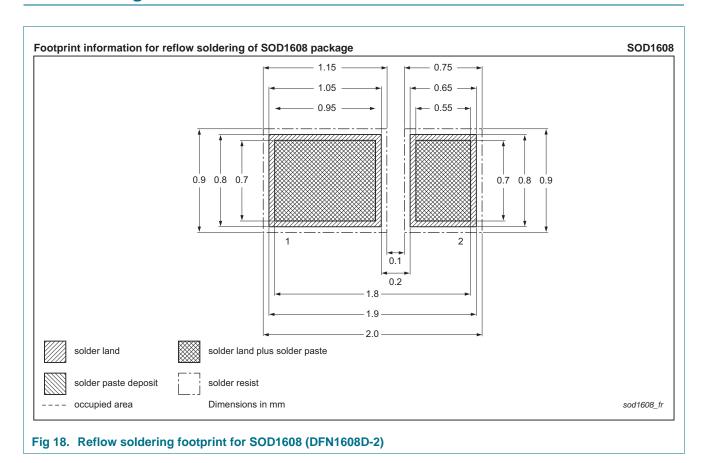
## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Soldering





# 11. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG4015EPK v.2	20120306	Product data sheet	-	PMEG4015EPK v.1
Modifications:	• <u>Fig 14.</u> and <u>1</u>	5: corrected title		
PMEG4015EPK v.1	20120302	Product data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PMEG4015EPK

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# PMEG4015EPK

## 40 V, 1.5 A low VF MEGA Schottky barrier rectifier

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## 13. Contact information

For more information, please visit:http://www.nxp.com

For sales office addresses, please send an email to:salesaddresses@nxp.com

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